# MT2312

# N-Channel Enhancement Mode Field Effect Transistor

## **Product Summary**

PRODUCT S	SUMMARY	
Vdss	Id	$RDS(ON) (m \Omega) Typ$
20V	4.5A	30@ VGS=4.5V
		50@ VGS=2.5V

## Features

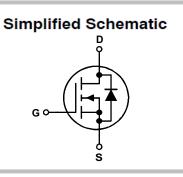
- Super high dense cell design for low RDS(ON)
- Rugged and reliable
- Simple drive requirement

#### Applications

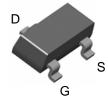
• LED Display



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MARKING DIAGRAM & PIN ASSIGNMENT



SOT-23

#### Absolute Maximum Ratings(T<sub>A</sub> = 25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	Vds	20	V
Gate-Source Voltage	VGS	±12	V
Drain Current-Continuous <sup>a</sup> @Tj=125°C	ID	3.6	А
- Pulse $d^b$	Ідм	12	А
Drain-source Diode Forward Current <sup>a</sup>	Is	1.25	А
Maximum Power Dissipation <sup>a</sup>	PD	1.25	W
Operating Junction and Storage Temperature Range	Tj,Tstg	-55 to 150	°C

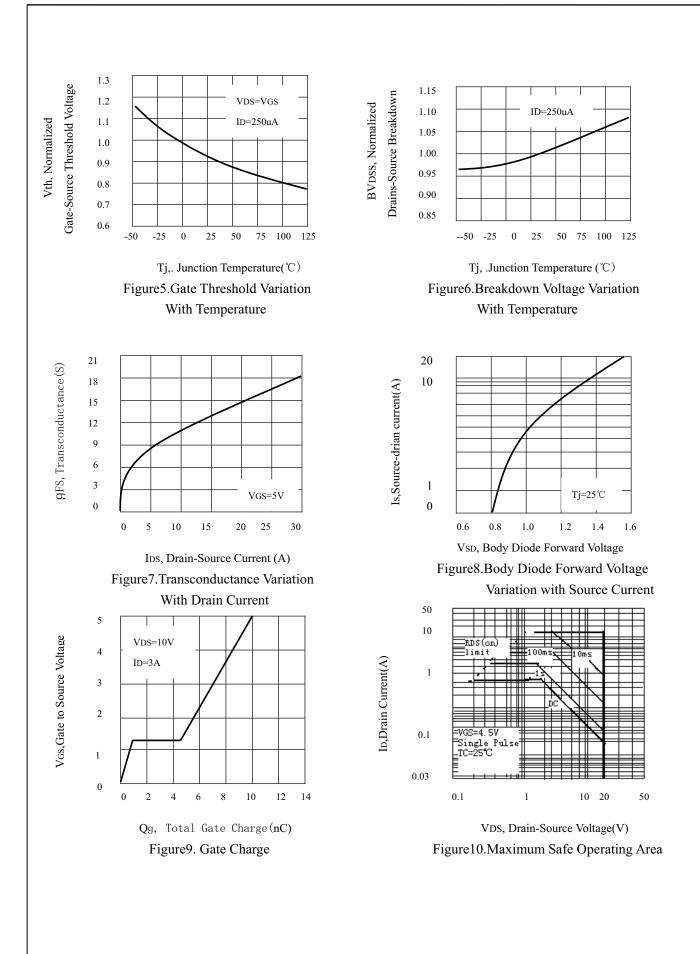
### THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to Ambient <sup>a</sup>	Rth JA	100	°C/W

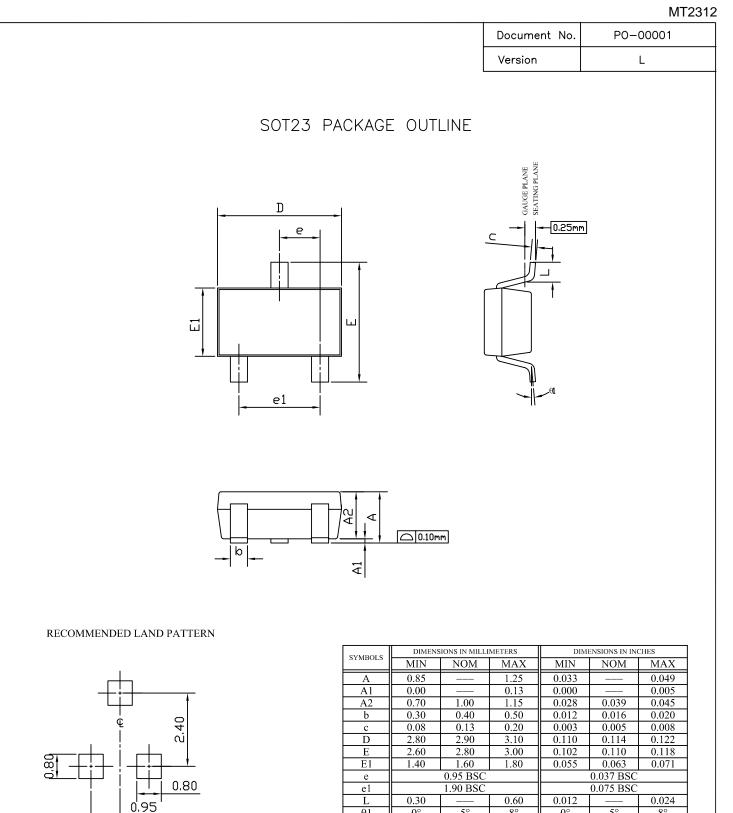
MT2312

Parameter	Symbol	Condition	Min	Тур	Max	Unit
OFF CHARACTERISTICS				I	1	
Drain-Source Breakdown Voltage	BVDSS	Vgs=0V,Id=250µA	20			V
Zero Gate Voltage Drain Current	Idss	VDS=16V,VGS=0V			1	μA
Gate-Body Leakage	Igss	VGS=±8V,VDS=0V			±100	nA
ON CHARACTERITICS						
Gate Threshold Voltage	VGs(th)	VDS=VGS,ID=-250µA	0.5	0.8	1.5	V
Drain-Source On-State Resistance	D	Vgs=4.5V,ID=2.8A		30	45	- m Ω
	Rds(on)	Vgs=2.5V,Id=2.0A		50	60	
Forward Transconductance	gfs	VGS=5V,ID=5A		5		S
DAYNAMIC CHARACTERISTICS				1	1	
Input Capacitance	Ciss	Vds=10V,Vgs=0V f=1.0MHz		586		pF
Output Capacitance	Coss			101		pF
Reverse Transfer Capacitance	Crss			59		pF
SWITCHING CHARACTERISISTICS				I	I	
Turn-On Delay Time	td(on)	V <sub>DD</sub> =10V		6.5		ns
Rise Time	tr	ID=3.6A, VGEN=4.5V RL=10ohm RGEN=10ohm		32.1		ns
Turn-Off Delay Time	td(off)			58.4		ns
Fall Time	tf			48		ns
Total Gate Charge	Qg	VDS=10V,ID=1A		6		nC
Gate-Source Charge	Qgs			1.35		nC
Gate-Drain Charge	Qgd	V <sub>GS</sub> =4.5V		1.5		nC

#### ELECTRICAL CHARACTERICS (TA=25°C unless otherwise noted) Symbol Condition Parameter Min Тур Max Unit DRAIN-SOURCE DIODE CHARACTERISTICS VGs=0V,Is=1.25A 0.84 V Diode Forward Voltage VSD 1.2 Notes Surface Mounted on FR4 Board, $t \leq 10$ sec a. Pulse Test: Pulse Width $\leq$ 300Us, Duty Cycle $\leq$ 2% b. Guaranteed by design, not subject to production testing. c. 10 25 Tj=125℃ 25°C vgs≓sv 8 20 /GS=10, 9, 8, 7, 6, 5, 4V ID, Drain Current (A) 6 ID, Drain Current(A) 15 VGS=2V 4 10 -55°C 2 5 0 0 0.5 1.0 1.5 2.0 2.5 3.0 1 2 З 4 5 6 n VDS, Drain-to-Source Voltage (V) VGS, Gate-to-source Voltage (V) Figure 1. Output Characteristics Figure 2. Transfer Characteristics 2.2 1100 Т VGS=4V RDS(ON), On-Resistance(m $\Omega$ ) 1.8 880 ID=3A 1.4 C,Capacitance(pF) 660 1.0 Ciss 440 0.6 220 0.2 Coss 0 Crss -50 -25 0 25 50 75 100 125 0 10 15 20 5 25 30 Tj(℃) VGS, Drain-to Source Voltage Figure4. On-Resistance Variation with Figure3. Capacitance Temperature



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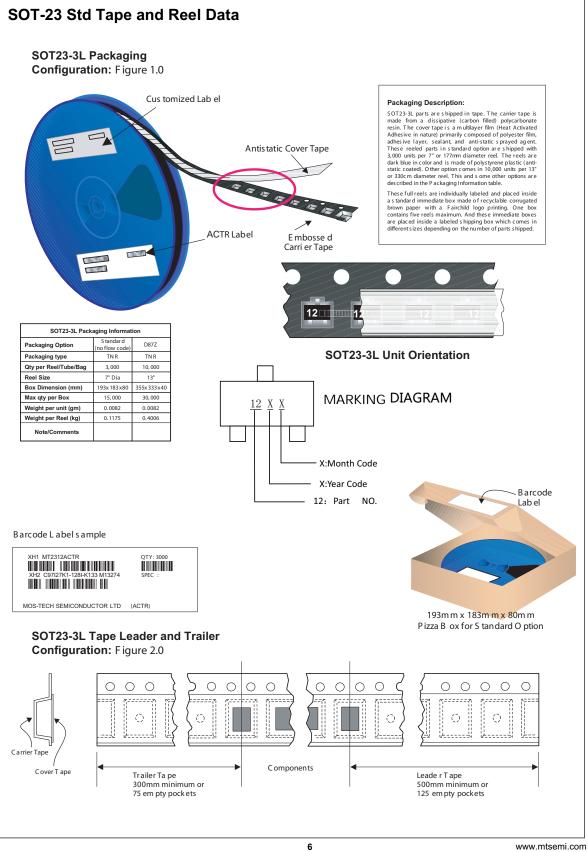


UNIT: mm

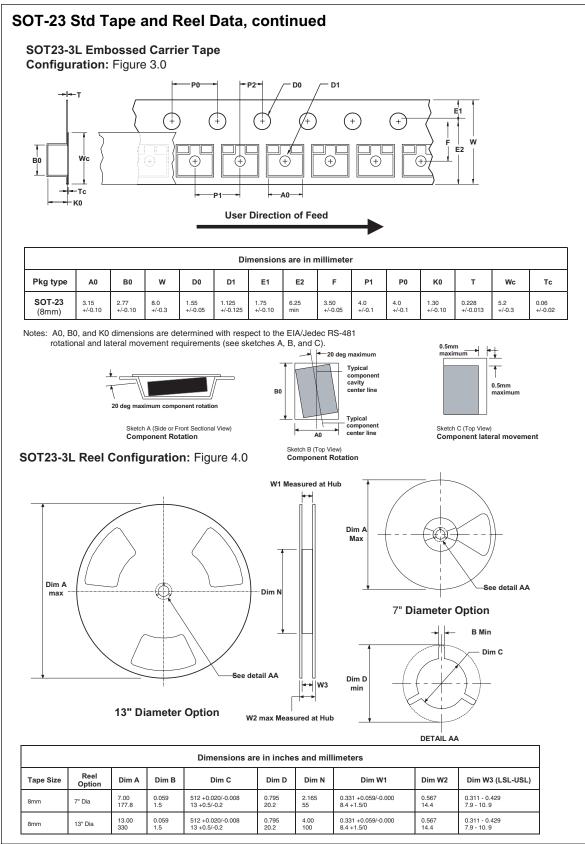
0.30 0.024 8° 5  $0^{\circ}$ θ1 8° 0°

NOTE

- 1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH OR GATE BURRS.
- MOLD FLASH AT THE NON-LEAD SIDES SHOULD BE LESS THAN 5 MILS EACH.
- 2. TOLERANCE ±0.100 mm (4 mil) UNLESS OTHERWISE SPECIFIED.
- 3. DIMENSION L IS MEASURED IN GAUGE PLANE.
- 4. CONTROLLING DIMENSION IS MILLIMETER. CONVERTED INCH DIMENSIONS
- ARE NOT NECESSARILY EXACT.
- 5. ALL DIMENSIONS ARE IN MILLIMETERS.



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